



ON Semiconductor®

# FDG8842CZ

## Complementary PowerTrench® MOSFET

Q1: 30V, 0.75A, 0.4Ω; Q2: -25V, -0.41A, 1.1Ω

### Features

Q1: N-Channel

- Max  $r_{DS(on)}$  = 0.4Ω at  $V_{GS} = 4.5V$ ,  $I_D = 0.75A$
- Max  $r_{DS(on)}$  = 0.5Ω at  $V_{GS} = 2.7V$ ,  $I_D = 0.67A$

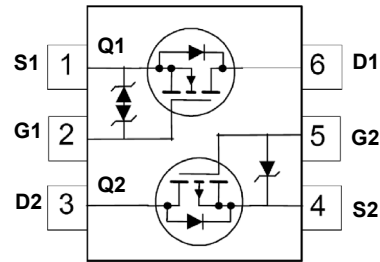
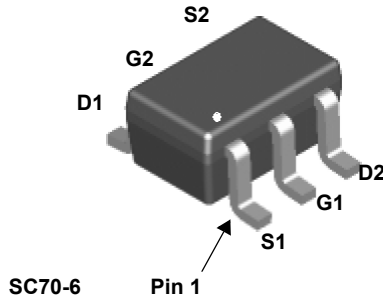
Q2: P-Channel

- Max  $r_{DS(on)}$  = 1.1Ω at  $V_{GS} = -4.5V$ ,  $I_D = -0.41A$
- Max  $r_{DS(on)}$  = 1.5Ω at  $V_{GS} = -2.7V$ ,  $I_D = -0.25A$
- Very low level gate drive requirements allowing direct operation in 3V circuits ( $V_{GS(th)} < 1.5V$ )
- Very small package outline SC70-6
- RoHS Compliant



### General Description

These N & P-Channel logic level enhancement mode field effect transistors are produced using ON Semiconductor's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance. This device has been designed especially for low voltage applications as a replacement for bipolar digital transistors and small signal MOSFETs. Since bias resistors are not required, this dual digital FET can replace several different digital transistors, with different bias resistor values.



### MOSFET Maximum Ratings $T_A = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Q1	Q2	Units
$V_{DS}$	Drain to Source Voltage	30	-25	V
$V_{GS}$	Gate to Source Voltage	$\pm 12$	-8	V
$I_D$	Drain Current -Continuous	0.75	-0.41	A
	-Pulsed	2.2	-1.2	
$P_D$	Power Dissipation for Single Operation (Note 1a) (Note 1b)	0.36		W
		0.30		
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150		$^\circ C$

### Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient Single operation (Note 1a)	350	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient Single operation (Note 1b)	415	

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
.42	FDG8842CZ	7"	8mm	3000 units

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$ $I_D = -250\mu\text{A}, V_{GS} = 0\text{V}$	Q1 Q2	30 -25			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$ $I_D = -250\mu\text{A}$ , referenced to $25^\circ\text{C}$	Q1 Q2		25 -21		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}$ $V_{DS} = -20\text{V}, V_{GS} = 0\text{V}$	Q1 Q2			1 -1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 12\text{V}, V_{DS} = 0\text{V}$ $V_{GS} = -8\text{V}, V_{DS} = 0\text{V}$	Q1 Q2			$\pm 10$ -100	$\mu\text{A}$ nA

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$ $V_{GS} = V_{DS}, I_D = -250\mu\text{A}$	Q1 Q2	0.65 -0.65	1.0 -0.8	1.5 -1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$ $I_D = -250\mu\text{A}$ , referenced to $25^\circ\text{C}$	Q1 Q2		-3.0 1.8		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 4.5\text{V}, I_D = 0.75\text{A}$ $V_{GS} = 2.7\text{V}, I_D = 0.67\text{A}$ $V_{GS} = 4.5\text{V}, I_D = 0.75\text{A}, T_J = 125^\circ\text{C}$ $V_{GS} = -4.5\text{V}, I_D = -0.41\text{A}$ $V_{GS} = -2.7\text{V}, I_D = -0.25\text{A}$ $V_{GS} = -4.5\text{V}, I_D = -0.41\text{A}, T_J = 125^\circ\text{C}$	Q1 Q2		0.25 0.29 0.36 0.87 1.20 1.22	0.4 0.5 0.6 1.1 1.5 1.9	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{V}, I_D = 0.75\text{A}$ $V_{DS} = -5\text{V}, I_D = -0.41\text{A}$	Q1 Q2		3 8		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	Q1 $V_{DS} = 10\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$	Q1 Q2		90 70	120 100	pF
$C_{oss}$	Output Capacitance	Q2 $V_{DS} = -10\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$	Q1 Q2		20 30	30 40	pF
$C_{rss}$	Reverse Transfer Capacitance		Q1 Q2		15 15	25 25	pF

**Switching Characteristics (note 2)**

$t_{d(on)}$	Turn-On Delay Time	Q1 $V_{DD} = 5\text{V}, I_D = 0.5\text{A}$	Q1 Q2		4 6	10 12	ns
$t_r$	Rise Time	$V_{GS} = 4.5\text{V}, R_{GEN} = 6\Omega$ Q2	Q1 Q2		1 16	10 29	ns
$t_{d(off)}$	Turn-Off Delay Time	$V_{DD} = -5\text{V}, I_D = -0.5\text{A}$ $V_{GS} = -4.5\text{V}, R_{GEN} = 6\Omega$	Q1 Q2		9 35	18 56	ns
$t_f$	Fall Time		Q1 Q2		1 40	10 64	ns
$Q_g$	Total Gate Charge	Q1	Q1 Q2		1.03 1.20	1.44 1.68	nC
$Q_{gs}$	Gate to Source Charge	$V_{GS} = 4.5\text{V}, V_{DD} = 5\text{V}, I_D = 0.75\text{A}$ Q2	Q1 Q2		0.29 0.31		nC
$Q_{gd}$	Gate to Drain "Miller" Charge	$V_{GS} = -4.5\text{V}, V_{DD} = -5\text{V}, I_D = -0.41\text{A}$	Q1 Q2		0.17 0.22		nC

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
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**Drain-Source Diode Characteristics and Maximum Ratings**

$I_S$	Maximum Continuous Drain-Source Diode Forward Current		Q1 Q2			0.3 -0.3	A
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0V, I_S = 0.3A$ (Note 2) $V_{GS} = 0V, I_S = -0.3A$ (Note 2)	Q1 Q2		0.76 -0.84	1.2 -1.2	V

**Notes:**

- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta JA}$  is determined by the user's board design.



a.  $350^\circ\text{C/W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper.



b.  $415^\circ\text{C/W}$  when mounted on a minimum pad of 2 oz copper.

Scale 1:1 on letter size paper.

- Pulse Test: Pulse Width  $< 300\mu\text{s}$ , Duty cycle  $< 2.0\%$ .

**Typical Characteristics (Q1 N-Channel)**  $T_J = 25^\circ\text{C}$  unless otherwise noted

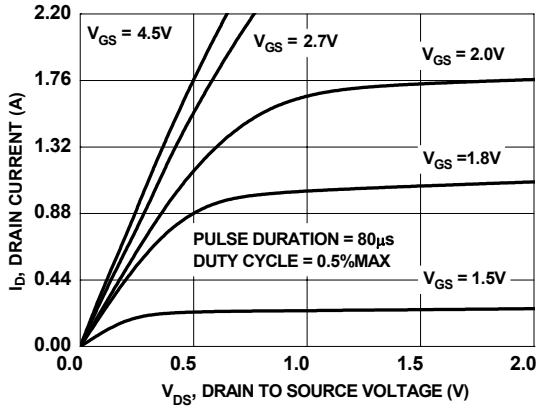


Figure 1. On-Region Characteristics

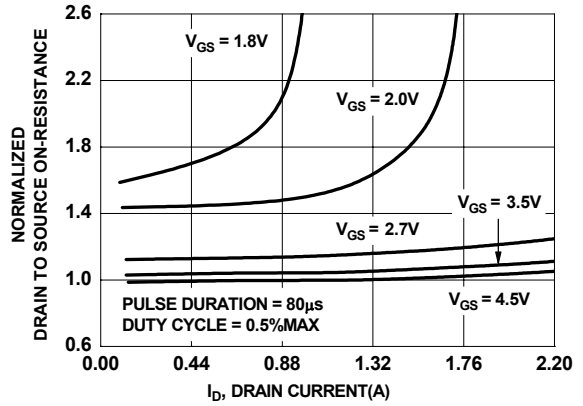


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

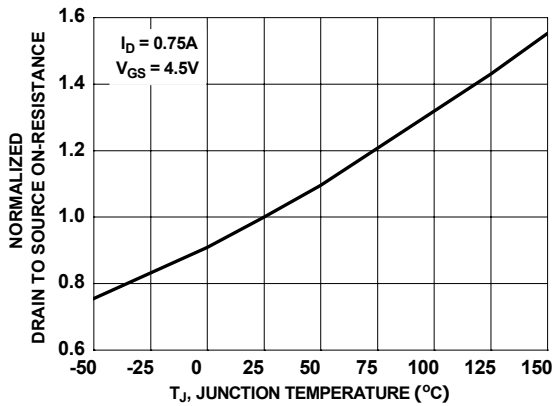


Figure 3. Normalized On-Resistance vs Junction Temperature

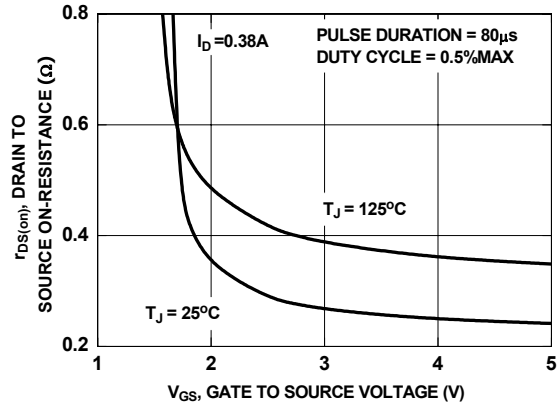


Figure 4. On-Resistance vs Gate to Source Voltage

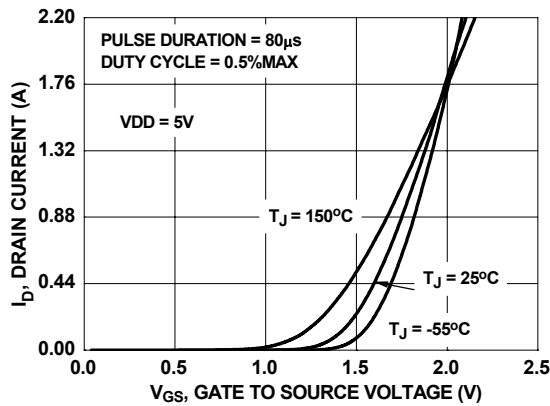


Figure 5. Transfer Characteristics

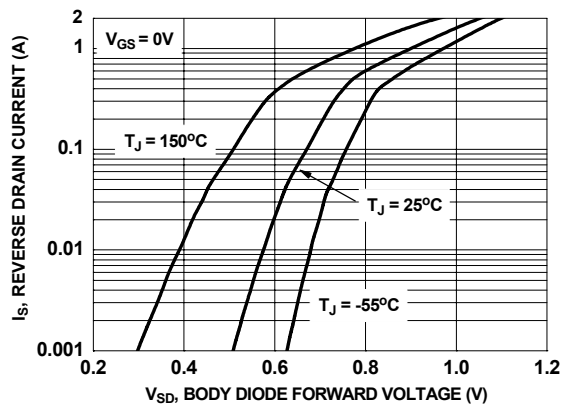
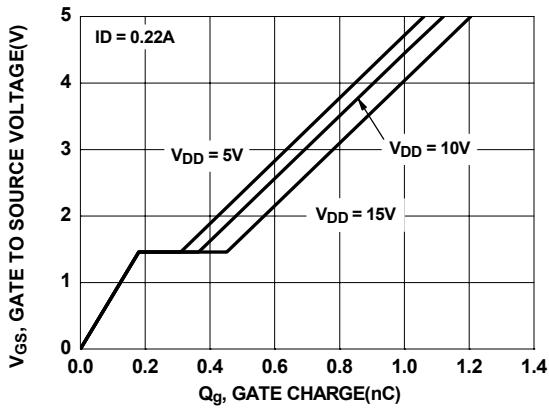
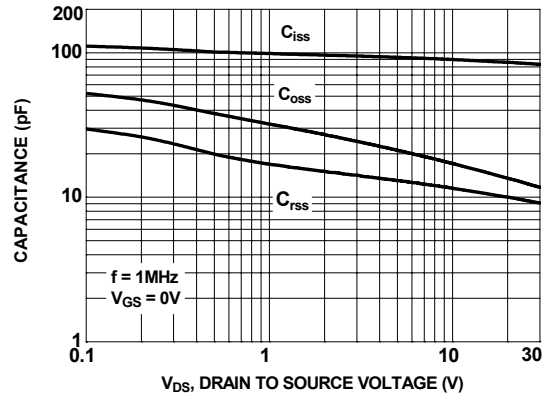


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

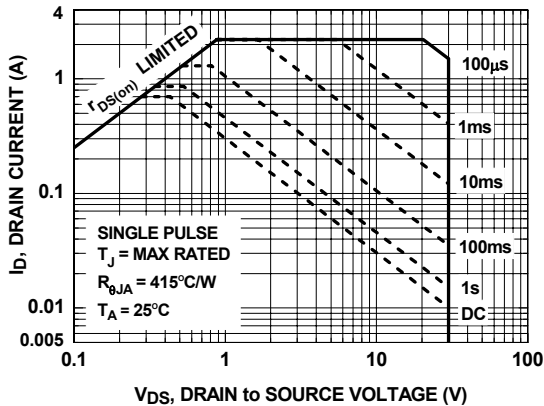
**Typical Characteristics (Q1 N-Channel)**  $T_J = 25^\circ\text{C}$  unless otherwise noted



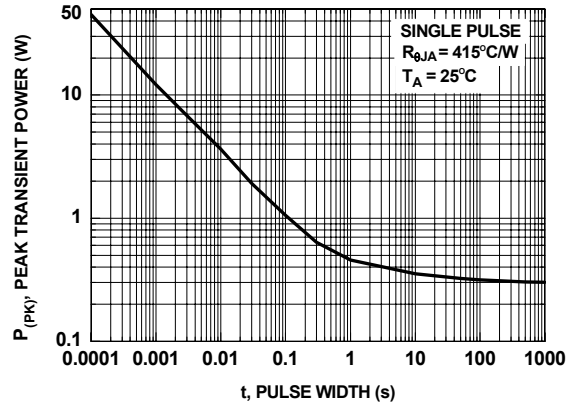
**Figure 7. Gate Charge Characteristics**



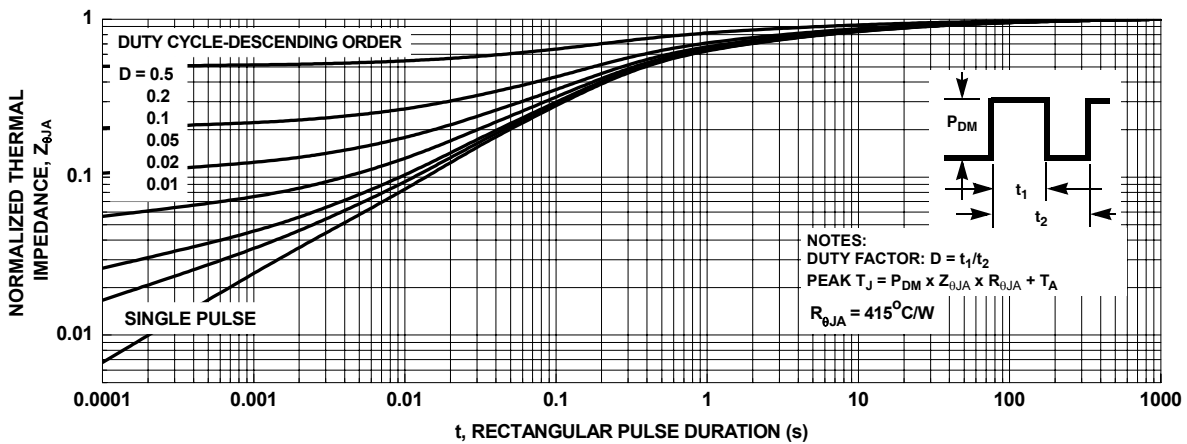
**Figure 8. Capacitance vs Drain to Source Voltage**



**Figure 9. Forward Bias Safe Operating Area**



**Figure 10. Single Pulse Maximum Power Dissipation**



**Figure 11. Transient Thermal Response Curve**

**Typical Characteristics (Q2 P-Channel)**  $T_J = 25^\circ\text{C}$  unless otherwise noted

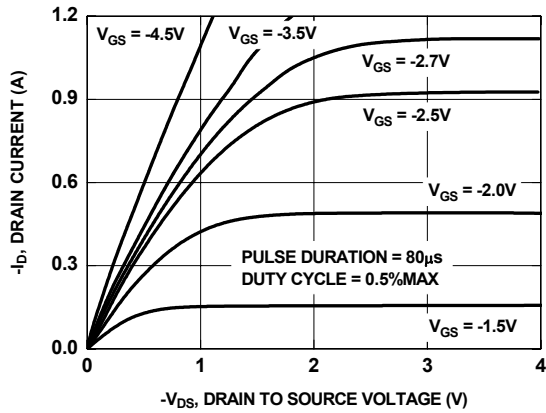


Figure 13. On Region Characteristics

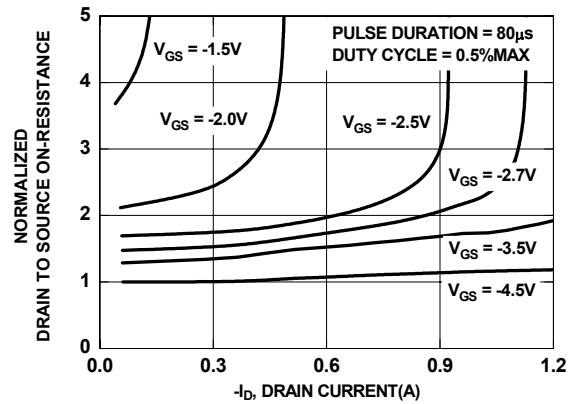


Figure 14. Normalized on-Resistance vs Drain Current and Gate Voltage

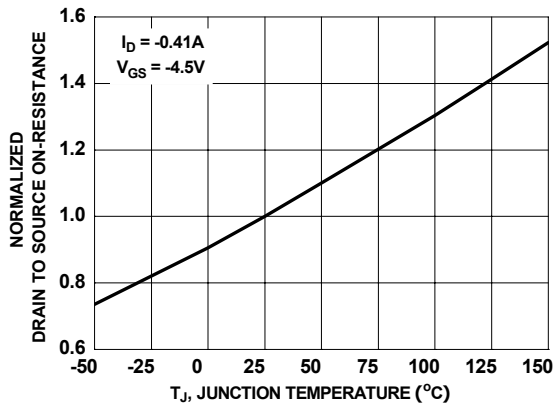


Figure 15. Normalized On Resistance vs Junction Temperature

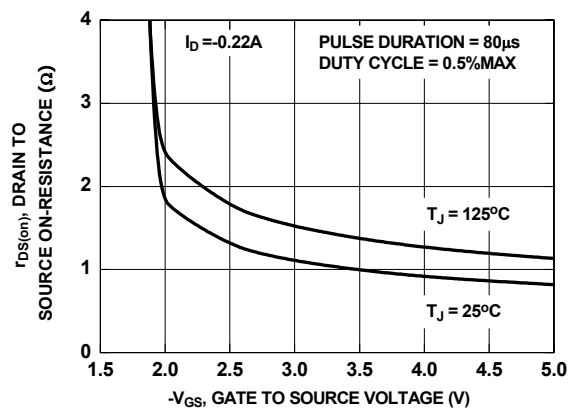


Figure 16. On-Resistance vs Gate to Source Voltage

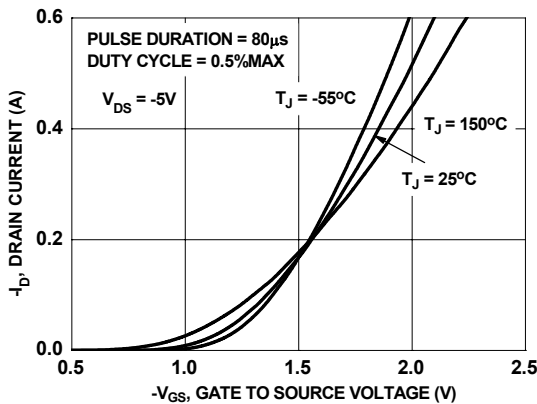


Figure 17. Transfer Characteristics

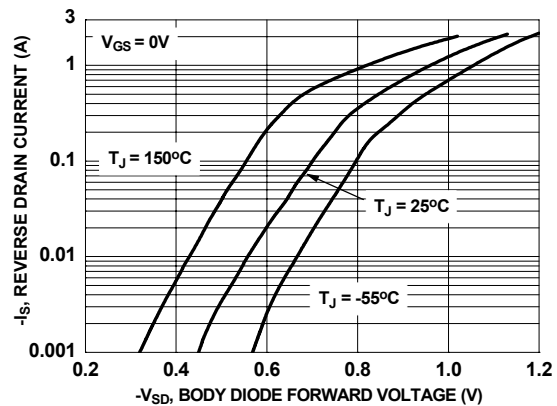
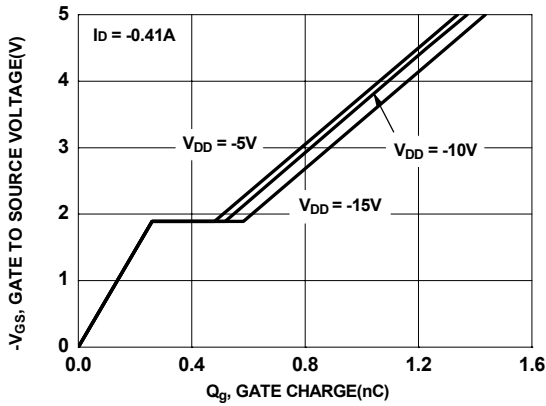
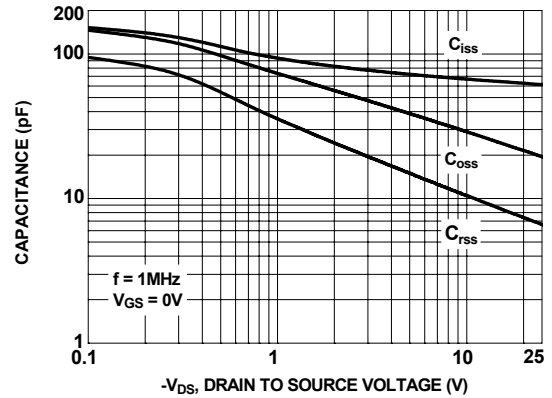


Figure 18. Source to Drain Diode Forward Voltage vs Source Current

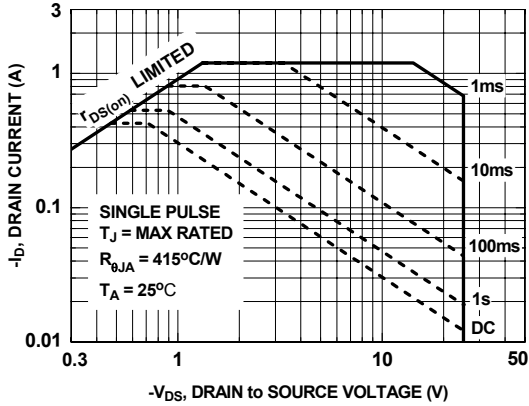
**Typical Characteristics(Q2 P-Channel)**  $T_J = 25^\circ\text{C}$  unless otherwise noted



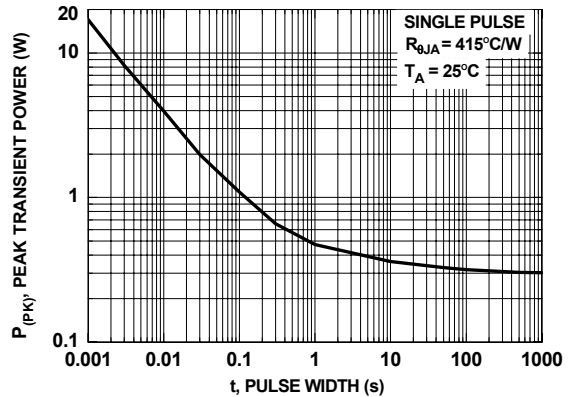
**Figure 19. Gate Charge Characteristics**



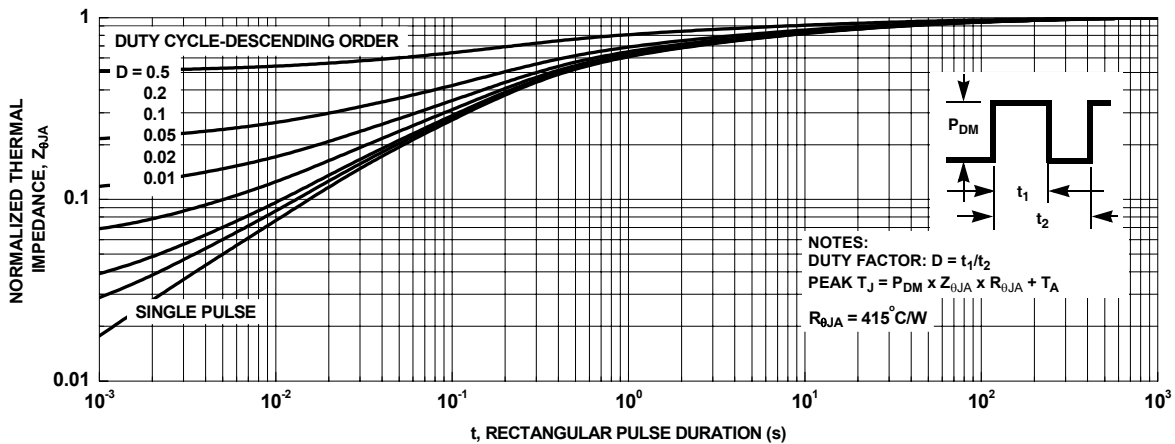
**Figure 20. Capacitance vs Drain to Source Voltage**



**Figure 21. Forward Bias Safe Operating Area**



**Figure 22. Single Pulse Maximum Power Dissipation**



**Figure 23. Transient Thermal Response Curve**

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